

IN THE CLAIMS

Please amend Claims 1, 3-5, 7 and 8 to read as follows.

1. (Currently Amended) A method for manufacturing a liquid ~~injecting~~ ejecting head, in which liquid flow paths are defined by combining an element substrate having a plurality of discharge energy generating elements for applying discharge energy to liquid with a nozzle member having a plurality of liquid discharge nozzle grooves and an opening communicating with said nozzle grooves, comprising the steps of:

preparing at least one material common to said element substrate having a first surface of <110> crystal face orientation as a base material of said nozzle member;

forming etching mask layers on ~~[[a]]~~ said first surface of the base material of said nozzle member ~~in which for forming said nozzle grooves are formed~~ and on a second surface opposite to said first surface, respectively;

forming a recessed portion corresponding to said opening in said second surface of the base material by patterning said mask layer on said second surface of the base material and by effecting etching in said second surface via said mask layer of said second surface; and

forming said nozzle grooves and said opening in the base material ~~[[and]]~~ for communicating said recessed portion with said nozzle grooves, by patterning said mask layer on said first surface of the base material and by effecting etching in said first surface and said recessed portion via said mask layer of said first surface and said mask layer of said second surface.

2. (Original) A method according to claim 1, wherein an etching amount t of etching for forming said recessed portion satisfies a relationship $t_w > t > t_w - t_n$ when it is assumed that a thickness of said nozzle member is t_w and a depth of said nozzle groove is t_n .

3. (Currently Amended) A method according to claim 1, wherein said nozzle member is a silicon substrate formed to have a surface of $\langle 110 \rangle$ crystal face orientation, and etching for the base material of said nozzle member is anisotropic etching ~~directing~~ directed perpendicular to a surface of the base material.

4. (Currently Amended) A method according to claim 3, wherein at least one of said mask ~~layer~~ layers is constituted by a silicon dioxide film.

5. (Currently Amended) A method for manufacturing a liquid ~~injecting~~ ejecting head, in which liquid flow paths are defined by combining an element substrate having a plurality of discharge energy generating elements for applying discharge energy to liquid with a nozzle member having a plurality of liquid discharge nozzle grooves and a liquid chamber ~~communicated~~ communicating with said nozzle grooves and an opening communicating with said liquid chamber, comprising the steps of:

preparing at least one material common to said element substrate having a first surface of $\langle 110 \rangle$ crystal face orientation as a base material of said nozzle member;

forming etching mask layers on ~~[[a]]~~ said first surface of the base material of said nozzle member ~~in which for forming said nozzle grooves are formed and said liquid chamber~~ and on a second surface opposite to said first surface, respectively;

forming a recessed portion corresponding to said opening in said second surface of the base material by patterning said mask layer on said second surface of the base material and by effecting etching in said second surface via said mask layer of said second surface; and

forming said nozzle grooves, ~~and said liquid chamber, and said opening~~ in the base material ~~[[and]]~~ for communicating said recessed portion with said liquid chamber, by patterning said mask layer on said first surface of the base material and by effecting etching in said first surface and said recessed portion via said mask layer of said first surface and said mask layer of said second surface.

6. (Original) A method according to claim 5, wherein an etching amount t of etching for forming said recessed portion satisfies a relationship $t_w > t > t_w - 2 \times t_n$ when it is assumed that a thickness of said nozzle member is t_w and a depth of said nozzle groove is t_n .

7. (Currently Amended) A method according to claim 5, wherein said nozzle member is a silicon substrate formed to have a surface of $\langle 110 \rangle$ crystal face orientation, and etching for the base material of said nozzle member is anisotropic etching ~~directing~~ directed perpendicular to a surface of the base material.

8. (Currently Amended) A method according to claim 7, wherein at least one of said mask ~~layer~~ layers is constituted by a silicon dioxide film.